

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A method for forming a MOSFET, said method comprises:

providing a wafer, wherein said wafer comprises a substrate;

forming a trench in said substrate;

forming a gate on a bottom of said trench;

forming a spacer on both sides of said gate and filling of said trench;

implanting a ion into said substrate which is on both sides of said spacer;

proceeding a first rapid thermal process to form a source/drain region and a source/drain extended region in said substrate;

forming a metal layer on said gate, said spacer, and said source /drain region;

proceeding a second rapid thermal process to form a silicide layer on said gate and said source/drain region; and

removing said unreacted metal layer.

Please amend claim 9 as follows:

9. (Amended) A method for forming a MOSFET, said method comprises:

providing a wafer, wherein said wafer comprises a substrate;

forming a trench in said substrate;

forming a gate on a bottom of said trench, wherein said gate comprises a gate oxide layer;

forming a spacer on a sidewall of said gate and said gate oxide layer and filling of said trench;

implanting a ion into said substrate which is on both sides of said spacer;

proceeding a first rapid thermal process to form a source/drain region and a source/drain extended region in said substrate;

forming a metal layer on said gate, said spacer, and said source /drain region;

proceeding a second rapid thermal process to form a silicide layer on said gate and said source/drain region; and

removing said unreacted metal layer and proceeding a third rapid thermal process.